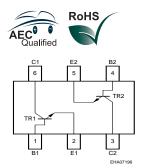
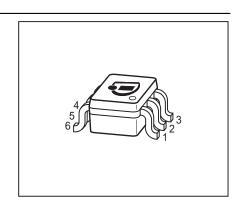


NPN Silicon RF Transistor*

- For low noise, high-gain broadband amplifiers at collector currents from 0.5 mA to 12 mA
- f_T = 8 GHz, F = 0.9 dB at 900 MHz
- Two (galvanic) internal isolated
 Transistors in one package
- For orientation in reel see package information below
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101
- * Short term description





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration					Package	
BFS481	RFs	1=B	2=E	3=C	4=B	5=E	6=C	SOT363

¹Pb-containing package may be available upon special request



Maximum	Ratings
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Parameter	Symbol	Value	Unit	
Collector-emitter voltage	$V_{\sf CEO}$	12	V	
Collector-emitter voltage	V_{CES}	20		
Collector-base voltage	V_{CBO}	20		
Emitter-base voltage	V_{EBO}	2		
Collector current	I _C	20	mA	
Base current	I _B	2		
Total power dissipation ¹⁾	P _{tot}	175	mW	
<i>T</i> _S ≤ 83 °C				
Junction temperature	$ \tau_{i} $	150	°C	
Ambient temperature	$ T_{A} $	-65 150		
Storage temperature	$T_{ m stq}$	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	≤ 380	K/W

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				,	
Collector-emitter breakdown voltage	V _{(BR)CEO}	12	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-emitter cutoff current	I _{CES}	-	-	100	μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	1	μΑ
$V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0					
DC current gain-	h _{FE}	70	100	140	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, pulse measured					

 $^{^{1}}T_{\mathrm{S}}$ is measured on the collector lead at the soldering point to the pcb

 $^{^2\}mbox{For calculation}$ of $R_{\mbox{\scriptsize thJA}}$ please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified Unit **Parameter Symbol Values** min. typ. max. AC Characteristics (verified by random sampling) 6 8 GHz Transition frequency f_{T} $I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz 0.23 0.4 pF Collector-base capacitance C_{cb} $V_{CR} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$, emitter grounded Collector emitter capacitance 0.13 C_{ce} $V_{CF} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BF} = 0$, base grounded C_{eb} 0.4 Emitter-base capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{CB} = 0$ collector grounded F dB Noise figure $I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, f = 900 MHz0.9 $I_{\rm C}$ = 2 mA, $V_{\rm CF}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, f = 1.8 GHz1.2 Power gain, maximum stable¹⁾ dB Gms 20 $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$, f = 900 MHz G_{ma} dB Power gain, maximum available²⁾ 15 $I_{\rm C} = 5 \text{ mA}, V_{\rm CE} = 8 \text{ V}, Z_{\rm S} = Z_{\rm Sopt}, Z_{\rm L} = Z_{\rm Lopt}$ f = 1.8 GHz $|S_{21e}|^2$ Transducer gain dB $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω , *f* = 900 MHz 16 $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm I}$ = 50 Ω , f = 1.8 MHz11

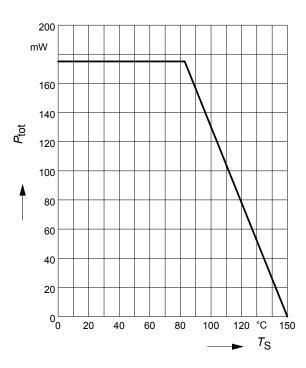
 $^{^{1}}G_{\text{ms}} = |S_{21} / S_{12}|$

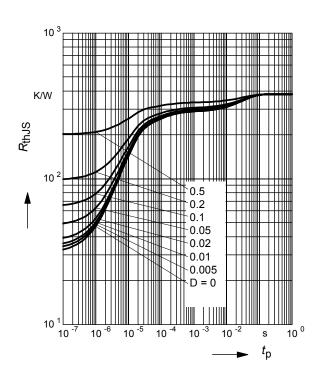
 $^{{}^{2}}G_{\text{ma}} = |S_{21e}/S_{12e}| (k-(k^{2}-1)^{1/2})$



Total power dissipation $P_{tot} = f(T_S)$

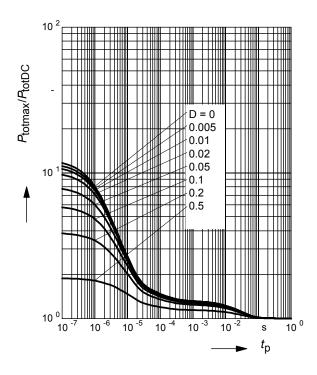
Permissible Pulse Load $R_{thJS} = f(t_p)$





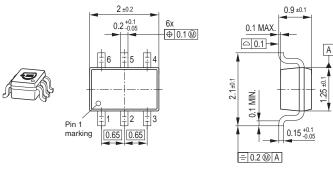
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$

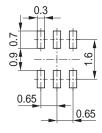




Package Outline

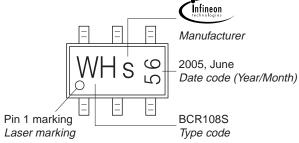


Foot Print



Marking Layout (Example)

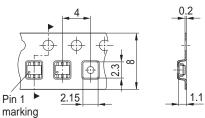
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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